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TABLE OF CONTENTS

1 Single-Crystal Aluminum Nitride Substrate Preparation from Bulk Crystals

J. Carlos Rojo, Leo J. Schowalter, and Kenneth Morgan*

8 Analysis of Electron Transport in a High-Mobility Freestanding GaN Substrate Grown by Hydride Vapor-Phase Epitaxy

F. Yun¹, H. Morkoç¹, D. L. Rode², K. T. Tsen³, L. Farina⁴, Ç. Kurdak⁴, S. S. Park⁵, and K. Y. Lee⁵

14 Characterization of very low defect-density free-standing GaN Substrate Grown by Hydride-Vapor-Phase-Epitaxy.

P. Visconti^{a,b}, M. A. Reschikov, K. M. Jones, F. Yun, R. Cingolanib, and H. Morkoç

20 High Spatial Resolution Thermal Conductivity investigation of SiC Wafers

D.I. FLORESCU, FRED H. POLLAK*, G.R. BRANDES**, B.E. LANDINI**, and A.D. SALANT***

26 InGaN-Channel FETs – Growth, Technology and Characteristics

E. Kohn, I. Daumiller*, M. Neuburger*, M. Seyboth, C. Kirchner, M. Kamp+*

37 Preparation of InN and InN-Based Heterostructures by Molecular Beam Epitaxy

Hai Lu, William J. Schaff, Jeonghyun Hwang, and Lester F. Eastman

43 MOCVD growth of GaN on flat and misoriented A-plane sapphire substrates

T. Someya, K. Hoshino, and Y. Arakawa

49 Electrical properties of MBE grown Si-doped Al_xGa_{1-x}N as a function of nominal Al mole fraction up to 0.5

M. Ahoujja,¹ Y. K. Yeo,¹ R. L. Hengehold,¹ and J. E. Van Nostrand²

55 MOCVD Growth of Ga(Al)N/InGaN/Ga(Al)N-Heterostructures: Influence of the Buffer Layer Al-Concentration and Growth Duration on the In-Incorporation in InGaN

Marco Schowalter, Brigitte Neubauer, Andreas Rosenauer, Dagmar Gerthsen, Oliver Schön¹, and Michael Heuken¹

61 Structural, optical and electrical properties of GaN films grown by metalorganic chemical vapor deposition on sapphire.

P. Visconti^{1,2}, M. A. Reschikov, F. Yun, K. M. Jones and H. Morkoç

- 67 Reduction of incorporation of B, Al, Ti and N in 4H-SiC epitaxial-layer grown by chemical vapor deposition at higher growth temperature**
Mitsuhiko Kushibe, Koh Masahara, Kazutoshi Kojima, Toshiyuki Ohno, Yuki Ishida, Tetsuo Takahashi, Johji Nishio, Takaya Suzuki, Tomoyuki Tanaka, Sadahumi Yoshida, Kazuo Arai
- 73 Influence of growth parameters on the nitrogen incorporation in 4H- and 6H-SiC epilayers grown by hot-wall chemical vapour deposition**
U. Forsberg, A. Henry, Ö. Danielsson, M.K. Linnarsson(1), and E. Janzen
- 79 Growth of 3C-SiC Layers on Silicon Substrates with a Novel Stress Relaxation Structure**
Yoshihiro Irokawa, Noboru Yamada, Masahito Kodama, and Tetsu Kachi
- 84 Surface Photovoltage Spectroscopy of InGaN/GaN/AlGaN Multiple Quantum Well Light Emitting Diodes**
B. Mishori, Martin Muñoz, L. Mourokh, and Fred H. Pollak
- 90 Characterization of GaN and Al_{0.35}Ga_{0.65}N/GaN Heterostructures by Scanning Kelvin Probe Microscopy**
G. Koley and M. G. Spencer
- 96 Ionization Energy and Electron Affinity of Clean and Oxidized Al_xGa_{1-x}N(0001) Surfaces**
H. Nienhaus¹, M. Schneider¹, S.P. Grabowski¹, W. Mönch¹, R. Dimitrov², O. Ambacher², and M. Stutzmann²
- 102 Hole Scattering in p-type Wurtzite Gallium Nitride**
J. D. Albrecht[†] and P. P. Ruden[‡]
- 108 Stress Effects in p-Type AlGaN/GaN Heterostructures**
Agustinus Sutandi, P. Paul Ruden, and Kevin F. Brennan¹
- 114 Characterization of Inversion Domains in GaN by Electric Force Microscopy in Conjunction with Transmission Electron Microscopy and Wet Chemical Etching**
F. Yun, P. Visconti^{1,2}, K. M. Jones, A. A. Baski, H. Morkoç, A. Passaseo², E. Piscopiello², M. Catalano¹ and R. Cingolani²
- 120 Influence of Spontaneous and Piezoelectric Polarizations on the Lattice Dynamics of III-Nitride Structures**
Jérôme Gleize, Jean Frandon, Marie A. Renucci, and Friedhelm Bechstedt¹
- 126 Persistent photocurrent effects in GaN/AlGaN multiquantum wells**
A. Bonfiglio¹, G. Traetta², M. Lomascolo³, A. Passaseo², and R. Cingolani²
- 132 Frequency Response of Trap States in an Al_xGa_{1-x}N/GaN Heterostructure Field-Effect Transistor Measured at the Nanoscale by dC/dV Spectroscopy**
Daniel M. Schaadt and Edward T. Yu

- 138 Spectroscopic Investigation of Traps Producing Current Collapse in AlGaN/GaN Hemt Structures**
P.B. Klein, S.C. Binari, K. Ikossi, A.E. Wickenden¹, D.D. Koleske and R.L. Henry, Naval
- 144 Extraction of Trap Characteristics from Excess Noise in GaN Devices**
Alexander A. Balandin
- 150 Recombination at surface states in GaN**
M. A. Reschikov, P. Visconti, I. K. M. Jones, and H. Morkoç
- 156 Photoluminescence and Excitation Spectra of Deep Defects in GaN**
Michael A. Reschikov, I. Richard J. Molnar² and Hadis Morkoç¹
- 162 Defect investigation of GaN thin films etched by photo-electrochemical and hot wet etching by atomic force and transmission electron microscopy**
P. Visconti^{1,2}, K. M. Jones, M. A. Reschikov, R. Cingolani², and H. Morkoç
- 168 Surface Evaluation of 6H-SiC after Doping by Diffusion**
Ying Gao, S. I. Soloviev, and T. S. Sudarshan
- 172 Infrared absorption and annealing behavior of semi-insulating 4H SiC HTCVD substrates**
B. Magnusson¹, A. Ellison², L. Storasta¹, and E. Janzen¹
- 178 The Influence of Contact Composition, Pretreatment, and Annealing Gas on the Ohmic Behavior of Ti/Al-Based Ohmic Contacts to n-Al0.4Ga0.6N**
K. O. Schweitz, T. G. Pribicko, S. E. Mohney, T. F. Isaacs-Smith¹, J. Williams¹, M. Pophristic², D. Gotthold², R. Birkhahn², and I. Ferguson²
- 184 Effects of Plasma Surface treatment on Ohmic Contact to n-GaN**
E.F. Chor and X. J. Kang
- 190 Stable Low Resistance Ohmic Contacts To p-GaN**
Mi-Ran Park¹ and Wayne A. Anderson²
- 196 Pt Schottky contacts on Ga- and N-face surfaces of free-standing GaN**
U. Karrer, C.R. Miskys, O. Ambacher, and M. Stutzmann
- 202 Structural and Electrical Characterization of Nickel Silicides Contacts on Silicon Carbide**
F. La Via#, F. Roccaforte§, V. Rainieri#, P. Musumeci, and L. Calcagno*.*
- 208 Optical Characterization of Mg- and Si-Implanted GaN**
James A. Fellows,¹ Yung Kee Yeo,¹ Robert L. Hengehold,¹ and Leonid Krasnobaev
- 214 Gadolinium Oxide Gate Dielectrics for GaN MOSFETs**
B.P. Gila, J.W. Johnson¹, K. N. Lee, V. Krishnamoorthy, S. Bates, C. R. Abernathy, F. Ren¹ and S. J. Pearton,

- 220 Fabrication of 0.1 ?m channel diamond Metal-Insulator-Semiconductor Field-Effect Transistor**
Hitoshi Umezawa, Yoshikazu Ohba, Hiroaki Ishizaka, Takuya Arima, Hirotada Taniuchi, Minoru Tachiki and Hiroshi Kawarada.
- 226 Low Temperature Epitaxial Growth of ZnO Layer on Sapphire by Plasma-Assisted Epitaxy**
Satoshi Yamauchi and Takashi Hariu
- 231 Effects of Beam Current Density on Ion Beam Synthesis of SiC**
*D.H. Chen, S.P. Wong**
- 237 Characterization of p-type 4H-SiC epitaxial layer grown on (11-20) substrate**
Kazutoishi Kojima^{1,3}, Toshiyuki Ohno^{1,3}, Mituhiro Kushibe^{1,3}, Koh Masahara^{1,3}, Yuuki Ishida^{1,2}, Tetuo Takahashi^{1,2}, Takaya Suzuki^{1,3}, Tomoyuki Tanaka^{1,3}, Sadafumi Yoshida^{1,2} and Kazuo Arai¹
- 243 Photo EPR Study of Trapping and Recombination Processes in Semi-Insulating 4H-SiC Crystals as Function of Temperature**
E.N. Kalabukhova¹, S.N. Lukin¹, A. Saxler², W.C. Mitchel², S.R. Smith², J.S. Solomon², and A.O. Evvarayev³
- 249 Single domain structure of 2H-AlN films on Si(001) substrates**
Joerg Jinschek, Vadim Lebedev, Ute Kaiser, and Wolfgang Richter
- 256 Raman scattering spectra in C-implanted GaN epilayers**
W. H. Sun¹, S. J. Chua¹, J. Zhang², L. S. Wang¹, M. S. Hao¹, K. M. Chen³, and G.G. Qin³
- 262 Photoluminescence and Raman Spectra of Flux Processed Bulk Single Crystal GaN**
Chae Ryong Cho¹, Sang Eon Park^{1,2}, Yong Chan Cho^{1,2} and Se-Young Jeong²
- 268 Carrier-Density Fluctuation Noise and the Interface Trap Density in GaN/AlGaN HFETs**
Dmitri Kotchetkov and Alexander A. Balandin
- 274 Current Gain of an AlGaN/GaN Heterojunction Bipolar Transistor**
Yumin Zhang, P. Paul Ruden
- 280 Design of Metal-Semiconductor-Metal Ultra-Violet Detector on Gallium Nitride**
Wenhua Gu, Soo Jin Chua, Xin Hai Zhang
- 285 Defects in 4H-SiC Induced by High Energy Helium Implantation**
Marie F. Beaufort, Erwan Oliviero, Marie L. David, Alain Declémé, Christian Blanchard,

- 289 Copper ohmic contacts to n-type SiC formed with pulsed excimer laser irradiation**
K. Abe, M. Sumitomo, O. Eryu, and K. Nakashima
- 294 Ab-Initio Calculation of the -SiC/Ni Interface**
A. BLASETTI¹, G. PROFET¹, S. PICOZZI¹, A. CONTINENZA¹, A. J. FREEMAN²
- 300 Components for AlGaN/GaN Power Amplifiers**
B. Jacobs¹, P. Wingelaar¹, M. Kramer¹, S. Falcone¹, F. Karouta¹, P. De Hek², E. Suijker², R. Van Dijk²
- 306 Modeling of a Breakdown Voltage in GaN Rectifiers and SiC Rectifiers**
*You- Sang Lee, Min-Koo Han and Yearn-Ik Choi**
- 312 X-band Silicon Carbide IMPATT Oscillator**
Konstantin V. Vassilevskii[#], Alexandr V. Zorenko¹, Konstantinos Zekentes²